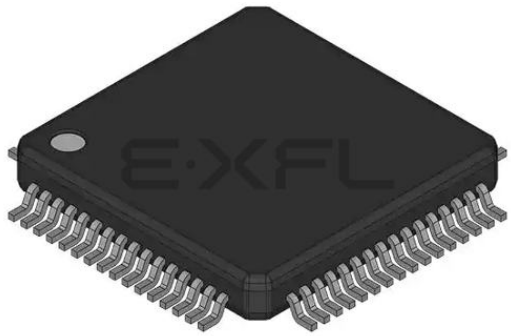

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	S08
Core Size	8-Bit
Speed	48MHz
Connectivity	I²C, SCI, SPI
Peripherals	LVD, POR, PWM, WDT
Number of I/O	33
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 6x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mc9s08mm32aclh

1 Devices in the MC9S08MM128 series

The following table summarizes the feature set available in the MC9S08MM128 series of MCUs.

Table 1. MC9S08MM128 series Features by MCU and Package

Feature	MC9S08MM128			MC9S08MM64	MC9S08MM32	MC9S08MM32A
Pin quantity	81	80	64	64	64	64
FLASH size (bytes)	131072			65535	32768	32768
RAM size (bytes)	12K			12K	4K	2K
Programmable Analog Comparator (PRACMP)	yes			yes	yes	yes
Debug Module (DBG)	yes			yes	yes	yes
Multipurpose Clock Generator (MCG)	yes			yes	yes	yes
Inter-Integrated Communication (IIC)	yes			yes	yes	yes
Interrupt Request Pin (IRQ)	yes			yes	yes	yes
Keyboard Interrupt (KBI)	16	16	6	6	6	6
Port I/O[1]	47	46	33	33	33	33
Dedicated Analog Input Pins	12			12	12	12
Power and Ground Pins	8			8	8	8
Time Of Day (TOD)	yes			yes	yes	yes
Serial Communications (SCI1)	yes			yes	yes	yes
Serial Communications (SCI2)	yes			yes	yes	yes
Serial Peripheral Interface 1 (SPI1 (FIFO))	yes			yes	yes	yes
Serial Peripheral Interface 2 (SPI2)	yes			yes	yes	yes
Carrier Modulator Timer pin (IRO)	yes			yes	yes	yes
TPM input clock pin (TPMCLK)	yes			yes	yes	yes
TPM1 channels	4			4	4	4
TPM2 channels	4	4	2	2	2	2
XOSC1	yes			yes	yes	yes
XOSC2	yes			yes	yes	yes
USB	yes			yes	yes	no
Programmable Delay Block (PDB)	yes			yes	yes	yes
SAR ADC differential channels[2]	4	4	3	3	3	3
SAR ADC single-ended channels	8	8	6	6	6	6
DAC ouput pin (DACO)	yes			yes	yes	yes
Voltage reference output pin (VREFO)	yes			yes	yes	yes
General Purpose OPAMP (OPAMP)	yes			yes	yes	yes
Trans-Impedance Amplifier (TRIAMP)	yes			yes	yes	yes

1 Port I/O count does not include two (2) output-only and one (1) input-only pins.

2 Each differential channel is comprised of 2 pin inputs.

A complete description of the modules included on each device is provided in the following table.

Table 2. Versions of On-Chip Modules

Module	Version
Analog-to-Digital Converter (ADC16)	1
General Purpose Operational Amplifier (OPAMP)	1
Trans-Impedance Operational Amplifier (TRIAMP)	1
Digital to Analog Converter (DAC)	1
Programmable Delay Block	1
Inter-Integrated Circuit (IIC)	3
Central Processing Unit (CPU)	5
On-Chip In-Circuit Debug/Emulator (DBG)	3
Multi-Purpose Clock Generator (MCG)	3
Low Power Oscillator (XOSCVLP)	1
Carrier Modulator Timer (CMT)	1
Programable Analog Comparator (PRACMP)	1
Serial Communications Interface (SCI)	4
Serial Peripheral Interface (SPI)	5
Time of Day (TOD)	1
Universal Serial Bus (USB)[1]	1
Timer Pulse-Width Modulator (TPM)	3
System Integration Module (SIM)	1
Cyclic Redundancy Check (CRC)	3
Keyboard Interrupt (KBI)	2
Voltage Reference (VREF)	1
Voltage Regulator (VREG)	1
Interrupt Request (IRQ)	3
Flash Wrapper	1
GPIO	2
Port Control	1

[1] USB Module not available on MC9S08MM32A devices.

The block diagram in Figure 1 shows the structure of the MC9S08MM128 series MCU.

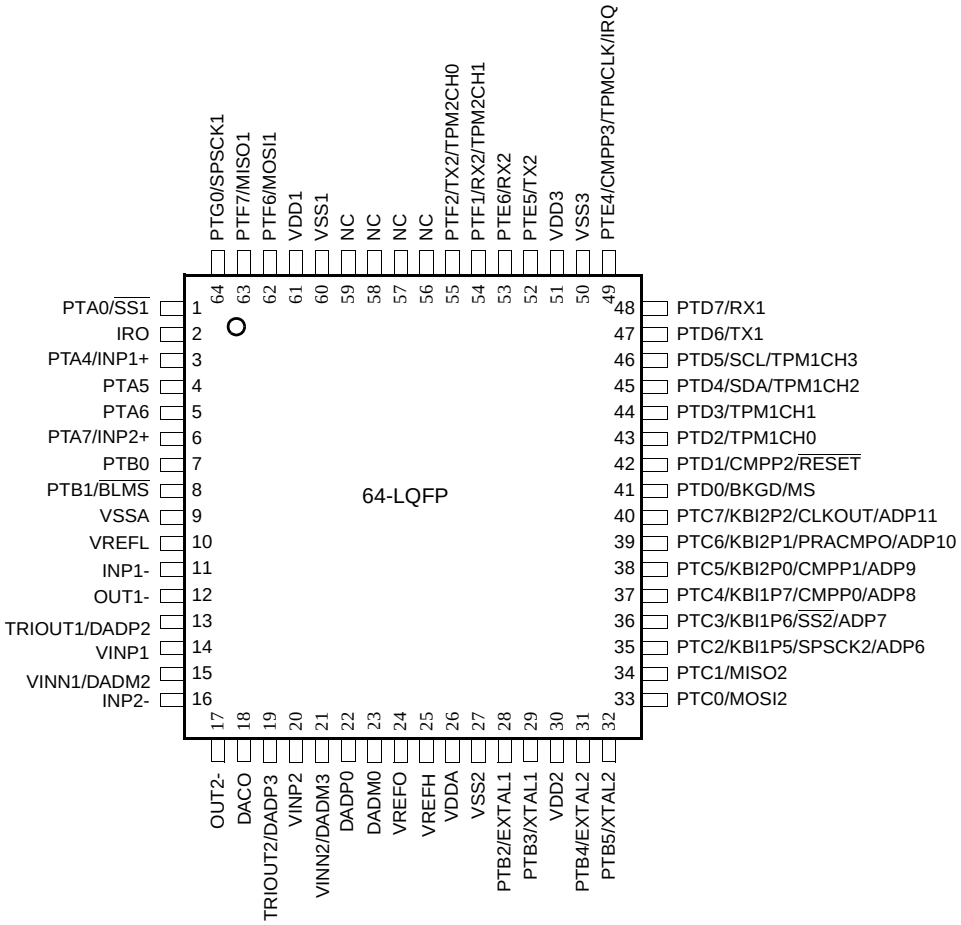

Figure 3. 64-Pin LQFP for MC9S08MM32A devices

1.1.3 81-Pin MAPBGA

The following figure shows the 81-pin MAPBGA pinout configuration.

	1	2	3	4	5	6	7	8	9
A	IRO	PTG0	PTF6	USB_DP	VBUS	VUSB33	PTF4	PTF3	PTE4
B	PTF7	PTA0	PTG1	USB_DM	PTF5	PTE7	PTF1	PTF0	PTE3
C	PTA4	PTA5	PTA6	PTA1	PTF2	PTE6	PTE5	PTE2	PTE1
D	INP1-	PTA7	PTB0	PTB1	PTA2	PTA3	PTD5	PTD7	PTE0
E	OUT1	VINN1	OUT2	VDD2	VDD3	VDD1	PTD2	PTD3	PTD6
F	VINP1	TRIOUT1	INP2-	VSS2	VSS3	VSS1	PTB7	PTC7	PTD4
G	DADP0	DACO	TRIOUT2	VINN2	VREFO	PTB6	PTC0	PTC1	PTC2
H	DADM0	DADM1	DADP1	VINP2	PTC3	PTC4	PTD0	PTC5	PTC6
J	VSSA	VREFL	VREFH	VDDA	PTB2	PTB3	PTD1	PTB4	PTB5

Figure 5. 81-Pin MAPBGA

Table 3. Package Pin Assignments (Continued)

Package			Default Function	ALT1	ALT2	ALT3	Composite Pin Name
81 MAPBGA	80 LQFP	64 LQFP					
J3	30	25	VREFH	—	—	—	VREFH
J4	31	26	VDDA	—	—	—	VDDA
F4	32	27	VSS2	—	—	—	VSS2
J5	33	28	PTB2	EXTAL1	—	—	PTB2/EXTAL1
J6	34	29	PTB3	XTAL1	—	—	PTB3/XTAL1
E4	35	30	VDD2	—	—	—	VDD2
J8	36	31	PTB4	EXTAL2	—	—	PTB4/EXTAL2
J9	37	32	PTB5	XTAL2	—	—	PTB5/XTAL2
G6	38	—	PTB6	KBI1P3	—	—	PTB6/KBI1P3
F7	39	—	PTB7	KBI1P4	—	—	PTB7/KBI1P4
G7	40	33	PTC0	MOSI2	—	—	PTC0/MOSI2
G8	41	34	PTC1	MISO2	—	—	PTC1/MISO2
G9	42	35	PTC2	KBI1P5	SPSCK2	ADP6	PTC2/KBI1P5/SPSCK2/ADP6
H5	43	36	PTC3	KBI1P6	$\overline{SS2}$	ADP7	PTC3/KBI1P6/$\overline{SS2}$/ADP7
H6	44	37	PTC4	KBI1P7	CMPP0	ADP8	PTC4/KBI1P7/CMPP0/ADP8
H8	45	38	PTC5	KBI2P0	CMPP1	ADP9	PTC5/KBI2P0/CMPP1/ADP9
H9	46	39	PTC6	KBI2P1	PRACMPO	ADP10	PTC6/KBI2P1/PRACMPO/ADP10
F8	47	40	PTC7	KBI2P2	CLKOUT	ADP11	PTC7/KBI2P2/CLKOUT/ADP11
H7	48	41	PTD0	BKGD	MS	—	PTD0/BKGD/MS
J7	49	42	PTD1	CMPP2	$\overline{RESET}$	—	PTD1/CMPP2/$\overline{RESET}$
E7	50	43	PTD2	TPM1CH0	—	—	PTD2TPM1CH0
E8	51	44	PTD3	TPM1CH1	—	—	PTD3/TPM1CH1
F9	52	45	PTD4	SDA	TPM1CH2	—	PTD4/SDA/TPM1CH2
D7	53	46	PTD5	SCL	TPM1CH3	—	PTD5/SCL/TPM1CH3
E9	54	47	PTD6	TX1	—	—	PTD6/TX1
D8	55	48	PTD7	RX1	—	—	PTD7/RX1
D9	56	—	PTE0	KBI2P3	—	—	PTE0/KBI2P3
C9	57	—	PTE1	KBI2P4	—	—	PTE1/KBI2P4
C8	58	—	PTE2	KBI2P5	—	—	PTE2/KBI2P5
B9	59	—	PTE3	KBI2P6	—	—	PTE3/KBI2P6
A9	60	49	PTE4	CMPP3	TPMCLK	IRQ	PTE4/CMPP3/TPMCLK/IRQ

Table 3. Package Pin Assignments (Continued)

Package			Default Function	ALT1	ALT2	ALT3	Composite Pin Name
81 MAPBGA	80 LQFP	64 LQFP					
F5	61	50	VSS3	—	—	—	VSS3
E5	62	51	VDD3	—	—	—	VDD3
C7	63	52	PTE5	TX2	—	—	PTE5/TX2
C6	64	53	PTE6	RX2	—	—	PTE6/RX2
B6	65	—	PTE7	TPM2CH3	—	—	PTE7/TPM2CH3
B8	66	—	PTF0	TPM2CH2	—	—	PTF0/TPM2CH2
B7	67	54	PTF1	RX2	TPM2CH1	—	PTF1/RX2/TPM2CH1
C5	68	55	PTF2	TX2	TPM2CH0	—	PTF2/TX2/TPM2CH0
A8	69	—	PTF3	SCL	—	—	PTF3/SCL
A7	70	—	PTF4	SDA	—	—	PTF4/SDA
B5	71	—	PTF5	KBI2P7	—	—	PTF5/KBI2P7
A6	72	56	VUSB33[1]	—	—	—	VUSB33
B4	73	57	USB_DM[2]	—	—	—	USB_DM
A4	74	58	USB_DP[3]	—	—	—	USB_DP
A5	75	59	VBUS[4]	—	—	—	VBUS
F6	76	60	VSS1	—	—	—	VSS1
E6	77	61	VDD1	—	—	—	VDD1
A3	78	62	PTF6	MOSI1	—	—	PTF6/MOSI1
B1	79	63	PTF7	MISO1	—	—	PTF7/MISO1
A2	80	64	PTG0	SPSCK1	—	—	PTG0/SPSCK1
B3	—	—	PTG1	—	—	—	PTG1

1 NC on MC9S08MM32A devices.
2 NC on MC9S08MM32A devices.
3 NC on MC9S08MM32A devices.
4 NC on MC9S08MM32A devices.

2.2 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in the following table may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

Table 5. Absolute Maximum Ratings

#	Rating	Symbol	Value	Unit
1	Supply voltage	V_{DD}	–0.3 to +3.8	V
2	Maximum current into V_{DD}	I_{DD}	120	mA
3	Digital input voltage	V_{In}	–0.3 to V_{DD} + 0.3	V
4	Instantaneous maximum current Single pin limit (applies to all port pins)[1, 2, 3]	I_D	± 25	mA
5	Storage temperature range	T_{stg}	–55 to 150	°C

1 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages, then use the larger of the two resistance values.

2 All functional non-supply pins are internally clamped to V_{SS} and V_{DD}.

3 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low (which would reduce overall power consumption).

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}).

2.3 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and it is user-determined rather than being controlled by the MCU design. In order to take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 6. Thermal Characteristics

#	Symbol	Rating	Value	Unit
1	T_A	Operating temperature range (packaged):		°C
		MC9S08MM128	–40 to 105	
		MC9S08MM64	–40 to 105	
		MC9S08MM32	–40 to 105	
		MC9S08MM32A	–40 to 105	
2	T_{JMAX}	Maximum junction temperature	135	°C
3	θ_{JA}	Thermal resistance[1,2,3,4] Single-layer board — 1s		°C/W
		81-pin MBGA	77	
		80-pin LQFP	55	
		64-pin LQFP	68	
4	θ_{JA}	Thermal resistance[1, 2, 3, 4] Four-layer board — 2s2p		°C/W
		81-pin MBGA	47	
		80-pin LQFP	40	
		64-pin LQFP	49	

1 Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

2 Junction to Ambient Natural Convection

3 1s — Single layer board, one signal layer

4 2s2p — Four layer board, 2 signal and 2 power layers

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA}) \qquad \textit{Eqn. 1}$$

where:

T_A = Ambient temperature, °C

θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W

$P_D = P_{int} + P_{I/O}$

$P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power

$P_{I/O}$ = Power dissipation on input and output pins — user determined

Table 9. DC Characteristics (Continued)

Num	Symbol	Characteristic	Condition	Min	Typ[1]	Max	Unit	C
20	V_{LVWH}	Low-voltage warning threshold — high range[9] — V_{DD} falling						
			—	2.36	2.46	2.56	V	P
		V_{DD} rising						
			—	2.36	2.46	2.56	V	P
21	V_{LVWL}	Low-voltage warning threshold — low range[9] — V_{DD} falling						
			—	2.11	2.16	2.22	V	P
		V_{DD} rising						
			—	2.16	2.23	2.27	V	P
22	V_{hys}	Low-voltage inhibit reset/recover hysteresis[10]	—	—	50	—	mV	C
23	V_{BG}	Bandgap Voltage Reference[11]	—	1.15	1.17	1.18	V	P

1 Typical values are measured at 25°C. Characterized, not tested

2 As the supply voltage rises, the LVD circuit will hold the MCU in reset until the supply has risen above V_{LVDL}.

3 Does not include analog module pins. Dedicated analog pins should not be pulled to V_{DD} or V_{SS} and should be left floating when not used to reduce current leakage.

4 Measured with $V_{In} = V_{DD}$.

5 All functional non-supply pins are internally clamped to V_{SS} and V_{DD} except PTD1.

6 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.

7 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if clock rate is very low (which would reduce overall power consumption).

8 Maximum is highest voltage that POR is guaranteed.

9 Run at 1 MHz bus frequency

10 Low voltage detection and warning limits measured at 1 MHz bus frequency.

11 Factory trimmed at V_{DD} = 3.0 V, Temp = 25°C

Table 10. Supply Current Characteristics (Continued)

#	Symbol	Parameter	Bus Freq	V_{DD} (V)	Typ[1]	Max	Unit	Temp (°C)	C
5	WI_{DD}	Wait mode supply current FEI mode, all modules OFF[3]							
			24 MHz	3	6.7	—	mA	–40 to 105	C
			20 MHz	3	5.6	—	mA	–40 to 105	T
			8 MHz	3	2.4	—	mA	–40 to 105	T
			1 MHz	3	1	—	mA	–40 to 105	T
6	$LPWI_{DD}$	Low-Power Wait mode supply current							
			16 KHz	3	10	40	µA	–40 to 105	T
7	$S2I_{DD}$	Stop2 mode supply current[4]							
			N/A	3	0.39	0.8	µA	–40 to 25	P
			N/A	3	2.4	4.5	µA	70	C
			N/A	3	7	11	µA	85	C
			N/A	3	16	22	µA	105	P
			N/A	2	0.2	0.45	µA	–40 to 25	C
			N/A	2	2	3.8	µA	70	C
			N/A	2	8	12	µA	85	C
			N/A	2	10	20	µA	105	C

Table 11. Typical Stop Mode Adders (Continued)

#	Parameter	Condition	Temperature (°C)					Units	C
			–40	25	70	85	105		
7	DAC[1]	High-Power mode; no load on DACO	369	377	377	390	410	µA	T
		Low-Power mode	50	51	51	52	60	µA	T
8	OPAMP[1]	High-Power mode	453	538	538	540	540	µA	T
		Low-Power mode	56	67	67	68	70	µA	T
9	TRIAMP[1]	High-Power mode	430	432	433	438	478	µA	T
		Low-Power mode	52	52	52	55	60	µA	T

1 Not available in stop2 mode.

2.7 PRACMP Electricals

Table 12. PRACMP Electrical Specifications

#	Characteristic	Symbol	Min	Typical	Max	Unit	C
1	Supply voltage	V_{PWR}	1.8	—	3.6	V	P
2	Supply current (active) (PRG enabled)	I_{DDACT1}	—	—	80	µA	D
3	Supply current (active) (PRG disabled)	I_{DDACT2}	—	—	40	µA	D
4	Supply current (ACMP and PRG all disabled)	I_{DDDIS}	—	—	2	nA	D
5	Analog input voltage	VAIN	V_{SS} – 0.3	—	V_{DD}	V	D
6	Analog input offset voltage	VAIO	—	5	40	mV	D
7	Analog comparator hysteresis	V_H	3.0	—	20.0	mV	D
8	Analog input leakage current	I_{ALKG}	—	—	1	nA	D
9	Analog comparator initialization delay	tAINIT	—	—	1.0	µs	D
10	Programmable reference generator inputs	V_{In2} (V_{DD25})	1.8	—	2.75	V	D
11	Programmable reference generator setup delay	t_{PRGST}	—	1	—	µs	D
12	Programmable reference generator step size	Vstep	0.75	1	1.25	LSB	D
13	Programmable reference generator voltage range	Vprgout	V_{In}/32	—	V_{in}	V	P

Table 14. DAC 12-Bit Operating Behaviors (Continued)

#	Characteristic	Symbol	Min	Typ	Max	Unit	C	Notes
9	DAC output voltage range high (high-power mode, no load, DAC set to 0x0FFF)	$V_{dacouth}$	V_{DACR}-100	—	—	mV	T	
10	Integral non-linearity error	INL	—	—	± 8	LSB	T	
11	Differential non-linearity error VDACR is > 2.4 V	DNL	—	—	± 1	LSB	T	
12	Offset error	E_O	—	±0.4	± 3	%FSR	T	Calculated by a best fit curve from V_{SS} + 100mV to V_{REFH} –100mV
13	Gain error, $V_{REFH} = V_{ext} = V_{DD}$	E_G	—	±0.1	± 0.5	%FSR	T	Calculated by a best fit curve from V_{SS} + 100mV to V_{REFH} –100mV
14	Power supply rejection ratio $V_{DD} \geq 2.4$ V	PSRR	60	—	—	dB	T	
15	Temperature drift of offset voltage (DAC set to 0x0800)	T_{co}	—	—	2	mV	T	See Typical Drift figure that follows.
16	Offset aging coefficient	A_c	—	—	8	µV/yr	T	

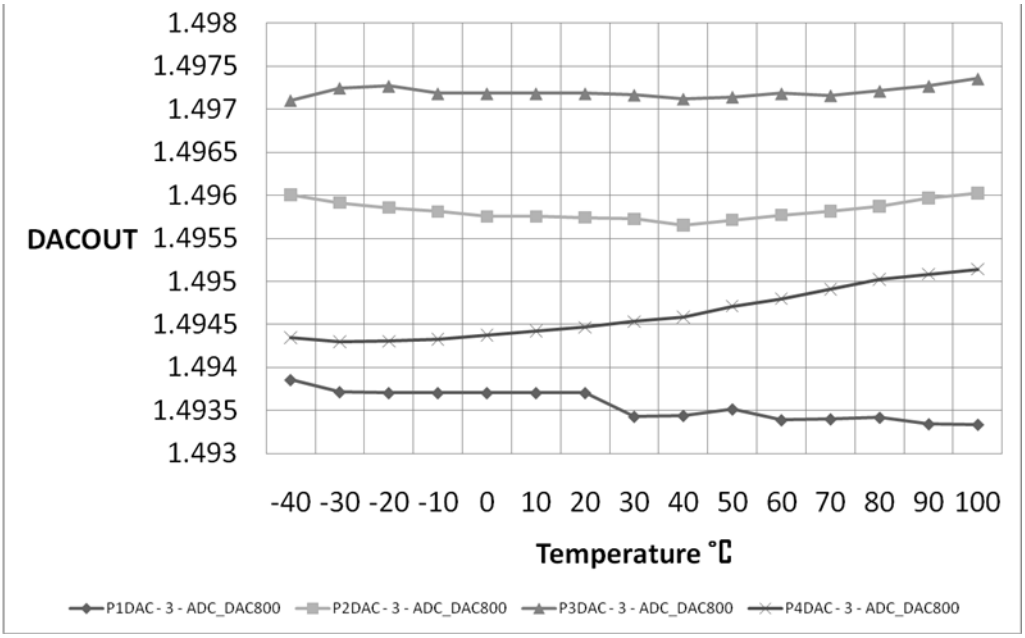

Figure 6. Offset at Half Scale vs Temperature

2.9 ADC Characteristics

Table 15. 16-Bit ADC Operating Conditions

#	Symb	Characteristic	Conditions	Min	Typ[1]	Max	Unit	C	Comment
1	V_{DDA}	Supply voltage	Absolute	1.8	—	3.6	V	D	
2	ΔV_{DDA}		Delta to V_{DD} (V_{DD}–V_{DDA})[2]	–100	0	+100	mV	D	
3	ΔV_{SSA}	Ground voltage	Delta to V_{SS} (V_{SS}–V_{SSA})[2]	–100	0	+100	mV	D	
4	V_{REFH}	Ref Voltage High		1.15	V_{DDA}	V_{DDA}	V	D	
5	V_{REFL}	Ref Voltage Low		V_{SSA}	V_{SSA}	V_{SSA}	V	D	
6	V_{ADIN}	Input Voltage		V_{REFL}	—	V_{REFH}	V	D	
7	C_{ADIN}	Input Capacitance	16-bit modes 8/10/12-bit modes	—	8 4	10 5	pF	T	
8	R_{ADIN}	Input Resistance		—	2	5	kΩ	T	
9	R_{AS}	Analog Source Resistance							External to MCU Assumes ADLSMP=0
		16-bit mode	f_{ADCK} > 8 MHz	—	—	0.5	kΩ	T	
			4 MHz < f_{ADCK} < 8 MHz	—	—	1	kΩ	T	
			f_{ADCK} < 4 MHz	—	—	2	kΩ	T	
		13/12-bit mode	f_{ADCK} > 8 MHz	—	—	1	kΩ	T	
			4 MHz < f_{ADCK} < 8 MHz	—	—	2	kΩ	T	
			f_{ADCK} < 4 MHz	—	—	5	kΩ	T	
		11/10-bit mode	f_{ADCK} > 8 MHz	—	—	2	kΩ	T	
			4 MHz < f_{ADCK} < 8 MHz	—	—	5	kΩ	T	
			f_{ADCK} < 4 MHz	—	—	10	kΩ	T	
		9/8-bit mode	f_{ADCK} > 8 MHz	—	—	5	kΩ	T	
			f_{ADCK} < 8 MHz	—	—	10	kΩ	T	

Table 15. 16-Bit ADC Operating Conditions (Continued)

#	Symb	Characteristic	Conditions	Min	Typ[1]	Max	Unit	C	Comment
10	f_{ADCK}	ADC Conversion Clock Frequency							
			ADLPC=0, ADHSC=1	1.0	—	8.0	MHz	D	
			ADLPC=0, ADHSC=0	1.0	—	5.0	MHz	D	
			ADLPC=1, ADHSC=0	1.0	—	2.5	MHz	D	

1 Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK}=1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

2 DC potential difference.

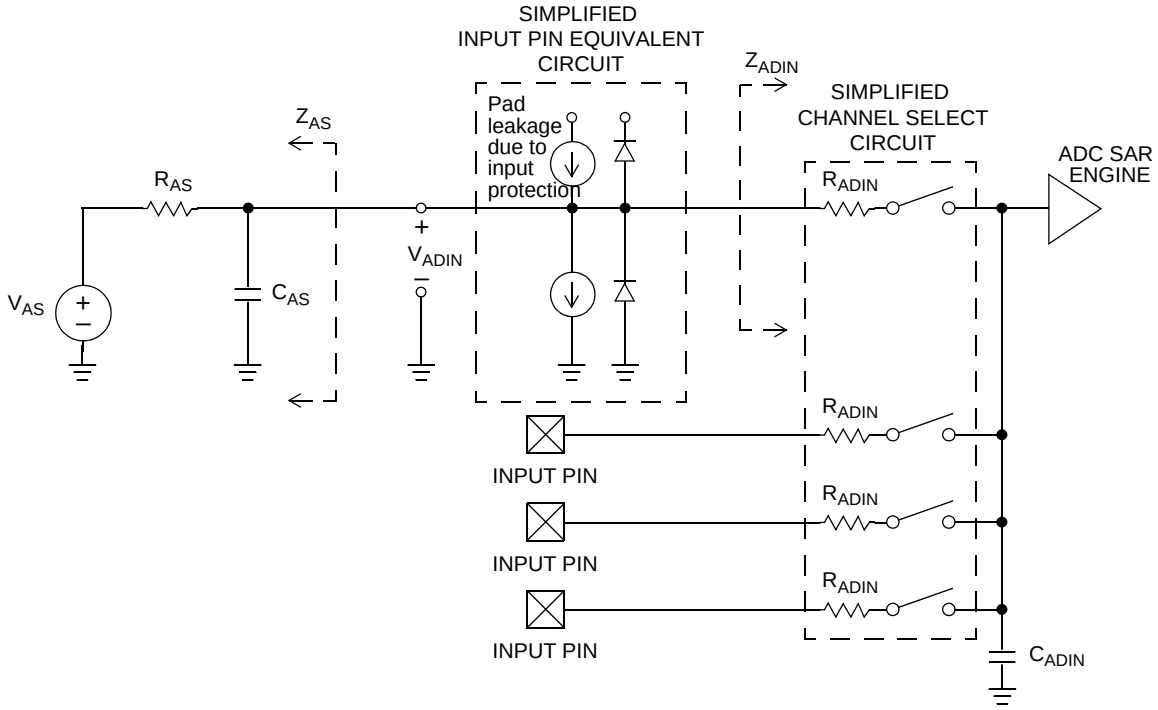

Figure 7. ADC Input Impedance Equivalency Diagram

2.10 MCG and External Oscillator (XOSC) Characteristics

Table 18. MCG (Temperature Range = –40 to 105°C Ambient)

#	Rating		Symbol	Min	Typical	Max	Unit	C
1	Internal reference startup time		t_{irefst}	—	55	100	µs	D
2	Average internal reference frequency	factory trimmed at VDD=3.0 V and temp=25°C	f_{int_ft}	—	31.25	—	kHz	C
		user trimmed		31.25	—	39.0625		C
3	DCO output frequency range — trimmed	Low range (DRS=00)	f_{dco_t}	16	—	20	MHz	C
		Mid range (DRS=01)		32	—	40		C
		High range[1] (DRS=10)		40	—	60		C
4	Resolution of trimmed DCO output frequency at fixed voltage and temperature	with FTRIM	$\Delta f_{dco\_res\_t}$	—	± 0.1	± 0.2	$\%f_{dco}$	C
		without FTRIM		—	± 0.2	± 0.4		C
5	Total deviation of trimmed DCO output frequency over voltage and temperature	over voltage and temperature	Δf_{dco_t}	—	±1.0	± 2	$\%f_{dco}$	P
		over fixed voltage and temp range of 0 – 70 °C		—	± 0.5	± 1		C
6	Acquisition time	FLL[2]	$t_{fll\_acquire}$	—	—	1	ms	C
		PLL[3]	$t_{pll\_acquire}$	—	—	1		D
7	Long term Jitter of DCO output clock (averaged over 2mS interval) [4]		C_{Jitter}	—	0.02	0.2	$\%f_{dco}$	C
8	VCO operating frequency		f_{vco}	7.0	—	55.0	MHz	D
9	PLL reference frequency range		f_{pll_ref}	1.0	—	2.0	MHz	D
10	Jitter of PLL output clock measured over 625ns [5]	Long term	$f_{pll\_jitter\_625ns}$	—	0.566[4]	—	$\%f_{pll}$	D
11	Lock frequency tolerance	Entry[6]	D_{lock}	± 1.49	—	± 2.98	%	D
		Exit[7]	D_{unl}	± 4.47	—	± 5.97		D
12	Lock time	FLL	t_{fll_lock}	—	—	$t_{fll\_acquire}$+ 1075(1/f_{int_t})	s	D
		PLL	t_{pll_lock}	—	—	$t_{pll\_acquire}$+ 1075(1/f_{pll_ref})		D
13	Loss of external clock minimum frequency - RANGE = 0		f_{loc_low}	(3/5) x f_{int_t}	—	—	kHz	D
14	Loss of external clock minimum frequency - RANGE = 1		f_{loc_high}	(16/5) x f_{int_t}	—	—	kHz	D

1 This should not exceed the maximum CPU frequency for this device which is 48 MHz.

2 This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bit is changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

Table 19. XOSC (Temperature Range = –40 to 105°C Ambient)

#	Characteristic		Symbol	Min	Typ[1]	Max	Unit	C
6	Crystal start-up time [4]	• Low range, low gain (RANGE = 0, HGO = 0)	$t_{CSTL-LP}$	—	200	—	ms	D
		• Low range, high gain (RANGE = 0, HGO = 1)	$t_{CSTL-HGO}$	—	400	—		D
		• High range, low gain (RANGE = 1, HGO = 0)[5]	$t_{CSTH-LP}$	—	5	—		D
		• High range, high gain (RANGE = 1, HGO = 1)[5]	$t_{CSTH-HGO}$	—	15	—		D

1 Data in Typical column was characterized at 3.0 V, 25°C or is typical recommended value.

2 When MCG is configured for FEE or FBE mode, input clock source must be divisible using RDIV to within the range of 31.25 kHz to 39.0625 kHz.

3 When MCG is configured for PEE or PBE mode, input clock source must be divisible using RDIV to within the range of 1 MHz to 2 MHz.

4 This parameter is characterized and not tested on each device. Proper PC board layout porcedures must be followed to achieve specifications.

5 4 MHz crystal.

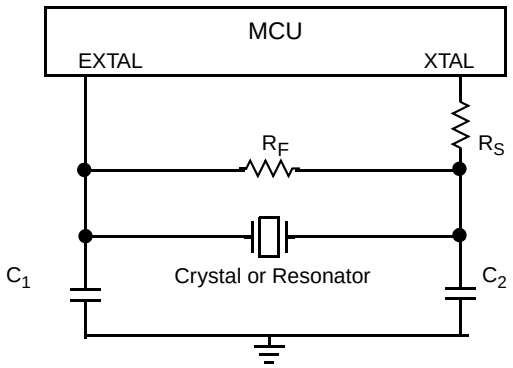

Table 20. Control Timing

#	Symbol	Parameter	Min	Typical[1]	Max	C	Unit
9	t_{Rise}, t_{Fall}	Port rise and fall time (load = 50 pF)[4], Low Drive					ns
		Slew rate control disabled (PTxSE = 0)	—	11	—	D	
		Slew rate control enabled (PTxSE = 1)	—	35	—	D	
		Slew rate control disabled (PTxSE = 0)	—	40	—	D	
		Slew rate control enabled (PTxSE = 1)	—	75	—	D	

1 Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.

2 This is the shortest pulse that is guaranteed to be recognized as a reset pin request. Shorter pulses are not guaranteed to override reset requests from internal sources.

3 This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized in that case.

4 Timing is shown with respect to 20% V_{DD} and 80% V_{DD} levels. Temperature range –40 °C to 105 °C.

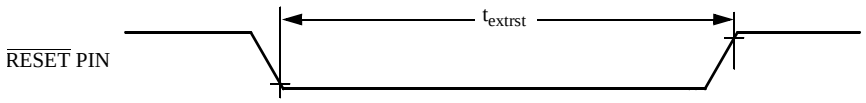

Figure 8. Reset Timing

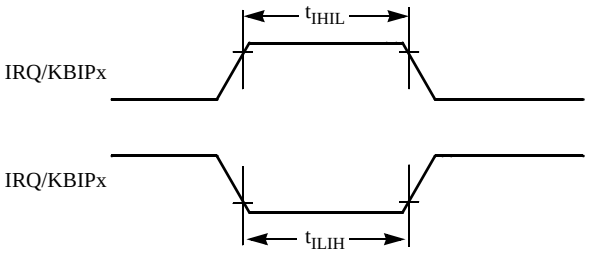

Figure 9. IRQ/KBIPx Timing

2.12 SPI Characteristics

Table 22 and Figure 12 through Figure 15 describe the timing requirements for the SPI system.

Table 22. SPI Timing

No.[1]	Characteristic[2]	Symbol	Min	Max	Unit	C
1	Operating frequency Master Slave	f_{op}	 $f_{Bus}/2048$ 0	 $f_{Bus}/2$ $f_{Bus}/4$	 Hz Hz	D
2	SPSCK period Master Slave	t_{SPSCK}	 2 4	 2048 —	 t_{cyc} t_{cyc}	D
3	Enable lead time Master Slave	t_{Lead}	 1/2 1	 — —	 t_{SPSCK} t_{cyc}	D
4	Enable lag time Master Slave	t_{Lag}	 1/2 1	 — —	 t_{SPSCK} t_{cyc}	D
5	Clock (SPSCK) high or low time Master Slave	t_{WSPSCK}	 $t_{cyc} - 30$ $t_{cyc} - 30$	 1024 t_{cyc} —	 ns ns	D
6	Data setup time (inputs) Master Slave	 t_{SU} t_{SU}	 15 15	 — —	 ns ns	D
7	Data hold time (inputs) Master Slave	 t_{HI} t_{HI}	 0 25	 — —	 ns ns	D
8	Slave access time[3]	t_a	—	1	t_{cyc}	D
9	Slave MISO disable time[4]	t_{dis}	—	1	t_{cyc}	D
10	Data valid (after SPSCK edge) Master Slave	t_v	 — —	 25 25	 ns ns	D
11	Data hold time (outputs) Master Slave	t_{HO}	 0 0	 — —	 ns ns	D
12	Rise time Input Output	 t_{RI} t_{RO}	 — —	 $t_{cyc} - 25$ 25	 ns ns	D
13	Fall time Input Output	 t_{FI} t_{FO}	 — —	 $t_{cyc} - 25$ 25	 ns ns	D

1 Numbers in this column identify elements in Figure 12 through Figure 15.

2 All timing is shown with respect to 20% V_{DD} and 70% V_{DD}, unless noted; 100 pF load on all SPI pins. All timing assumes slew rate control disabled and high drive strength enabled for SPI output pins.

3 Time to data active from high-impedance state.

4 Hold time to high-impedance state.

2.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the Flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see the Memory chapter in the Reference Manual for this device (MC9S08MM128RM).

Table 23. Flash Characteristics

#	Characteristic	Symbol	Min	Typical	Max	Unit	C
1	Supply voltage for program/erase –40°C to 105°C	$V_{prog/erase}$	1.8	—	3.6	V	D
2	Supply voltage for read operation	V_{Read}	1.8	—	3.6	V	D
3	Internal FCLK frequency[1]	f_{FCLK}	150	—	200	kHz	D
4	Internal FCLK period (1/FCLK)	t_{Fcyc}	5	—	6.67	µs	D
5	Byte program time (random location)[2]	t_{prog}	9			t_{Fcyc}	P
6	Byte program time (burst mode)[2]	t_{Burst}	4			t_{Fcyc}	P
7	Page erase time[2]	t_{Page}	4000			t_{Fcyc}	P
8	Mass erase time[2]	t_{Mass}	20,000			t_{Fcyc}	P
9	Program/erase endurance[3] T_L to T_H = –40°C to + 105°C T = 25°C		10,000 —	— 100,000	— —	cycles	C
10	Data retention[4]	t_{D_ret}	15	100	—	years	C

1 The frequency of this clock is controlled by a software setting.

2 These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

3 **Typical endurance for flash** was evaluated for this product family on the HC9S12Dx64. For additional information on how Freescale defines typical endurance, please refer to Engineering Bulletin EB619, *Typical Endurance for Nonvolatile Memory*.

4 **Typical data retention** values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale defines typical data retention, please refer to Engineering Bulletin EB618, *Typical Data Retention for Nonvolatile Memory.*

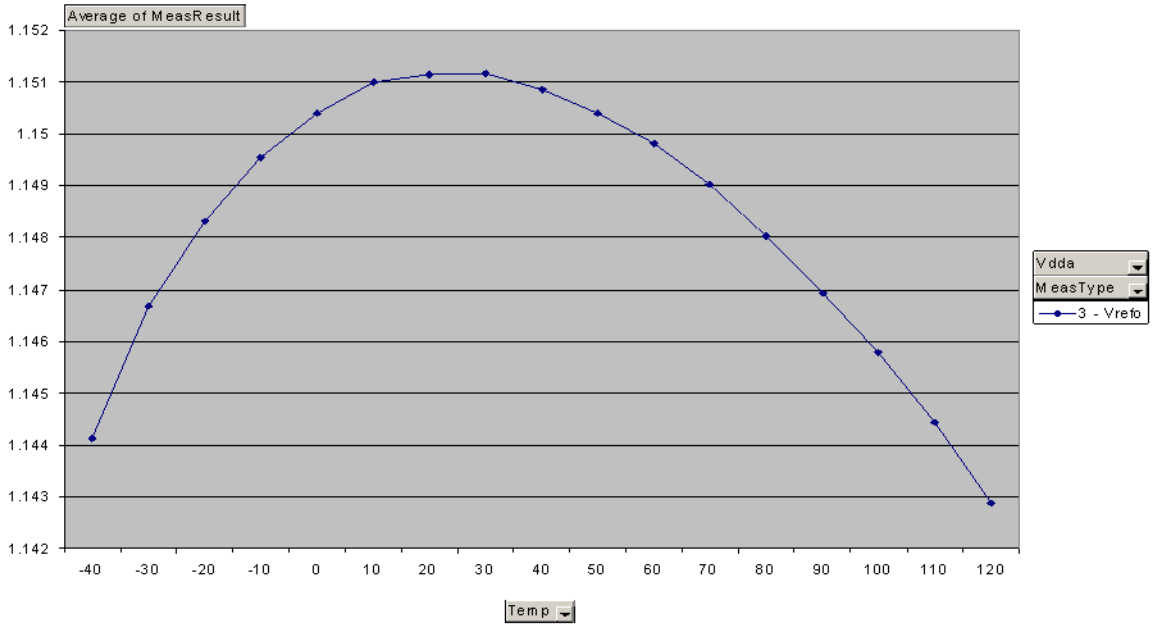

Figure 16. Typical VREF Output vs. Temperature

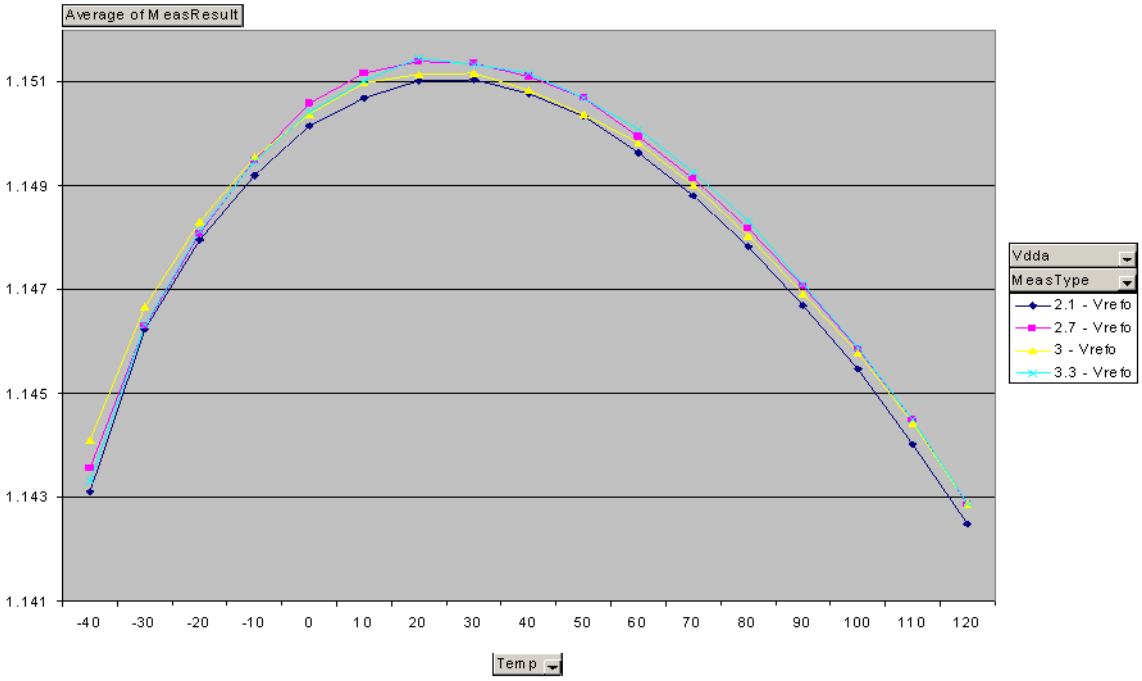

Figure 17. Typical VREF Output vs. V_{DD}